

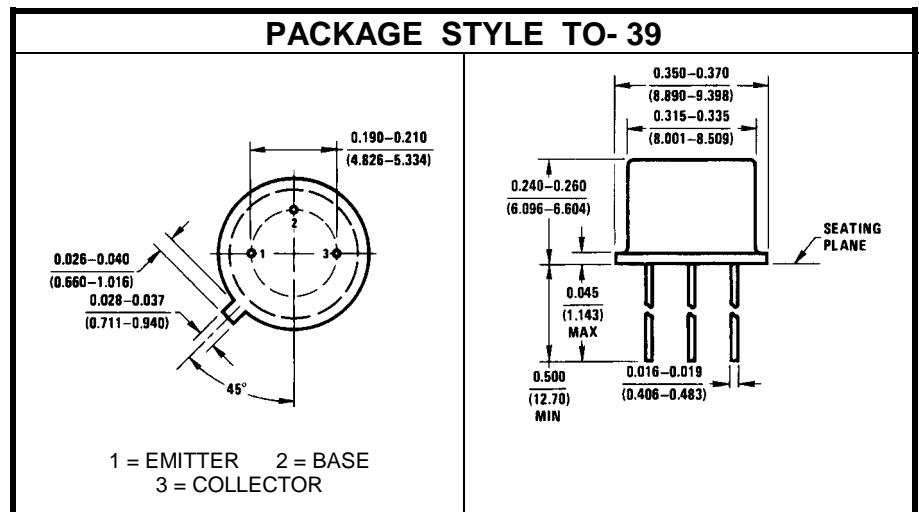
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **ASI 2N3553** is Designed for Amplifier, Oscillator and Driver Applications Covering VHF-UHF Frequency.

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	40 V
P_{DISS}	7.0 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	$25^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA		40			V
I_{CEX}	$V_{CE} = 65$ V	$V_{BE} = -1.5$ V			1.0	mA
	$V_{CE} = 30$ V	$V_{BE} = -1.5$ V			5.0	mA
	$T_C = 200^\circ C$					
I_{CEO}	$V_{CE} = 30$ V				100	μA
I_{EBO}	$V_{EB} = 4.0$ V				100	μA
h_{FE}	$V_{CE} = 5.0$ V	$I_C = 250$ mA	10			---
$V_{CE(SAT)}$	$I_C = 250$ mA	$I_B = 50$ mA			1.0	V
C_{ob}	$V_{CB} = 30$ V	$f = 1.0$ MHz			10	pF
f_t	$V_{CE} = 28$ V	$I_C = 100$ mA		500		MHz
P_{in}	$V_{CE} = 28$ V	$P_{out} = 2.5$ W	$f = 175$ MHz		250	mW
G_p				10		dB
η_c				50		%